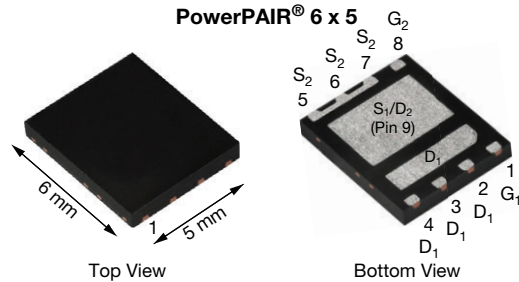


Dual N-Channel 25 V (D-S) MOSFETs



FEATURES

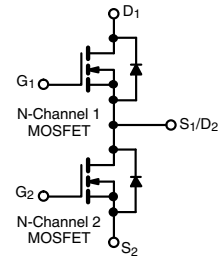
- TrenchFET® Gen IV power MOSFETs
- 100 % R_g and UIS tested
- Optimized Q_{gs}/Q_{gs} ratio improves switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC



PRODUCT SUMMARY		
	CHANNEL-1	CHANNEL-2
V _{DS} (V)	25	25
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.00480	0.00220
R _{DS(on)} max. (Ω) at V _{GS} = 4.5 V	0.00790	0.00335
Q _g typ. (nC)	5.9	12.5
I _D (A) ^{a, 9}	40	60
Configuration	Dual	

ORDERING INFORMATION	
Package	PowerPAIR 6 x 5
Lead (Pb)-free and halogen-free	SiZ926DT-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	CHANNEL-1	CHANNEL-2	UNIT	
Drain-source voltage	V _{DS}	25	25	V	
Gate-source voltage	V _{GS}	+16, -12	+16, -12		
Continuous drain current (T _J = 150 °C)	I _D	T _C = 25 °C	40 ^a	60 ^a	A
		T _C = 70 °C	40 ^a	60 ^a	
		T _A = 25 °C	22 ^{b, c}	37 ^{b, c}	
		T _A = 70 °C	17.5 ^{b, c}	30 ^{b, c}	
Pulsed drain current (100 μs pulse width)	I _{DM}	100	170		
Continuous source drain diode current	I _S	T _C = 25 °C	16.8	33.6	
		T _A = 25 °C	3.2 ^{b, c}	4 ^{b, c}	
Single pulse avalanche current	I _{AS}	15	28		
Single pulse avalanche energy	E _{AS}	11	39	mJ	
Maximum power dissipation	P _D	T _C = 25 °C	20.2	40	W
		T _C = 70 °C	12.9	25.8	
		T _A = 25 °C	3.8 ^{b, c}	4.8 ^{b, c}	
		T _A = 70 °C	2.4 ^{b, c}	3.1 ^{b, c}	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) ^d		260			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	CHANNEL-1		CHANNEL-2		UNIT
		TYP.	MAX.	TYP.	MAX.	
Maximum junction-to-ambient ^{b, f}	R _{thJA}	26	33	21	26	°C/W
Maximum junction-to-case (drain)	R _{thJC}	4.7	6.2	2.5	3.1	

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 68 °C/W for channel-1 and 57 °C/W for channel-2
- T_C = 25 °C



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-1	25	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-2	25	-	-	
V_{DS} Temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1	-	19	-	mV/ $^\circ\text{C}$
		$I_D = 250\text{ }\mu\text{A}$	Ch-2	-	15	-	
$V_{GS(th)}$ Temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1	-	4.9	-	
		$I_D = 250\text{ }\mu\text{A}$	Ch-2	-	4.6	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1.1	-	2.2	V
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-2	1.1	-	2.4	
Gate source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = +16\text{ V}, -12\text{ V}$	Ch-1	-	-	100	nA
			Ch-2	-	-	100	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	-	1	μA
		$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}$	Ch-2	-	-	1	
		$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	Ch-1	-	-	10	
		$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	Ch-2	-	-	10	
On-state drain current ^b	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20	-	-	A
		$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-2	20	-	-	
Drain-source on-state resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	Ch-1	-	0.00380	0.00480	Ω
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2	-	0.00173	0.00220	
		$V_{GS} = 4.5\text{ V}, I_D = 3\text{ A}$	Ch-1	-	0.00640	0.00790	
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-2	-	0.00265	0.00335	
Forward transconductance ^b	g_{fs}	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	Ch-1	-	40	-	S
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2	-	55	-	
Dynamic ^a							
Input capacitance	C_{iss}	Channel-1 $V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, f = 1\text{ MHz}$ Channel-2 $V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, f = 1\text{ MHz}$	Ch-1	-	925	-	pF
			Ch-2	-	2150	-	
Output capacitance	C_{oss}		Ch-1	-	310	-	
			Ch-2	-	800	-	
Reverse transfer capacitance	C_{rss}		Ch-1	-	52	-	
			Ch-2	-	100	-	
C_{rss}/C_{iss} ratio			Ch-1	-	0.056	0.115	
			Ch-2	-	0.047	0.095	
Total gate charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	Ch-1	-	12.5	19	nC
		$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2	-	27	41	
		$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1	-	5.9	8.9	
		$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-2	-	12.5	19	
Gate-source charge	Q_{gs}	Channel-1 $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1	-	2.5	-	
		Ch-2	-	5.4	-		
Gate-drain charge	Q_{gd}	Channel-2 $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-1	-	1.2	-	
		Ch-2	-	2.1	-		
Output charge	Q_{oss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	5	-	
			Ch-2	-	13	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	Ch-1	0.18	0.92	1.9	Ω
			Ch-2	0.12	0.6	1.2	



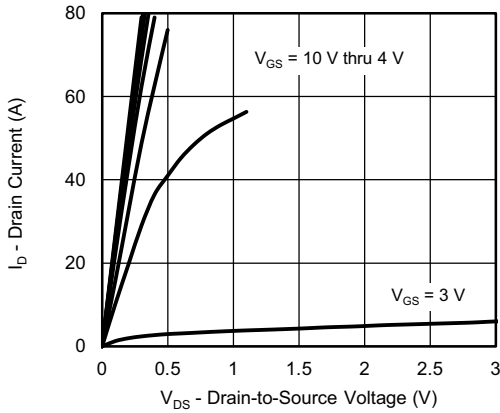
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Dynamic ^a							
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	8	20	ns
			Ch-2	-	10	20	
Rise time	t _r	Channel-1 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	20	40	
			Ch-2	-	20	40	
Turn-off delay time	t _{d(off)}	Channel-2 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	12	25	
			Ch-2	-	17	35	
Fall time	t _f	Channel-2 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	8	20	
			Ch-2	-	8	20	
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	12	25	
			Ch-2	-	16	35	
Rise time	t _r	Channel-1 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	47	100	
			Ch-2	-	40	80	
Turn-off delay time	t _{d(off)}	Channel-2 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	6	15	
			Ch-2	-	13	30	
Fall time	t _f	Channel-2 V _{DD} = 10 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	12	25	
			Ch-2	-	12	25	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	Ch-1	-	-	16.8	A
			Ch-2	-	-	33.6	
Pulse diode forward current (t = 100 μs)	I _{SM}		Ch-1	-	-	100	
			Ch-2	-	-	170	
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	Ch-1	-	0.81	1.2	V
		I _S = 8 A, V _{GS} = 0 V	Ch-2	-	0.77	1.2	
Body diode reverse recovery time	t _{rr}		Ch-1	-	25	50	ns
			Ch-2	-	20	40	
Body diode reverse recovery charge	Q _{rr}	Channel-1 I _F = 5 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	15	30	nC
		Channel-1 I _F = 5 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-2	-	15	30	
Reverse recovery fall time	t _a	Channel-2 I _F = 8 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	13.5	-	ns
		Channel-2 I _F = 8 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-2	-	13	-	
Reverse recovery rise time	t _b		Ch-1	-	11.5	-	
			Ch-2	-	7	-	

Notes

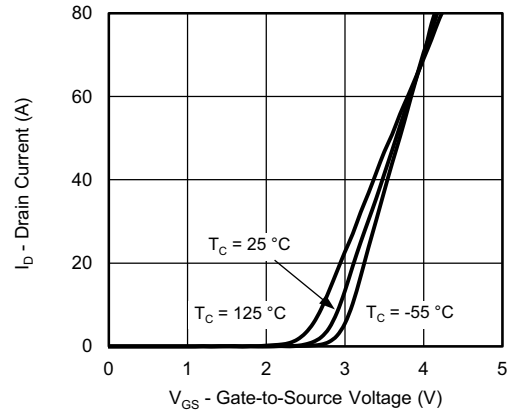
- a. Guaranteed by design, not subject to production testing
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

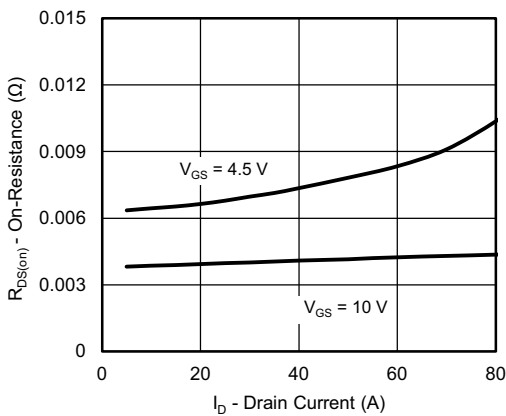
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



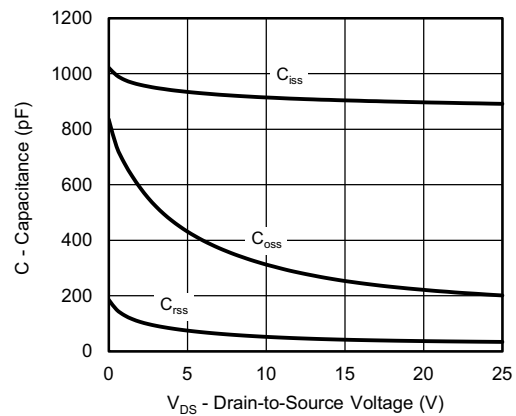
Output Characteristics



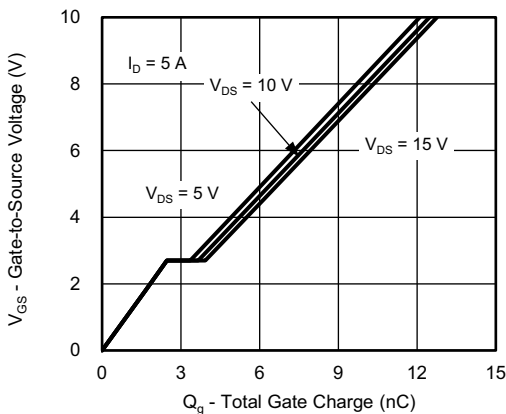
Transfer Characteristics



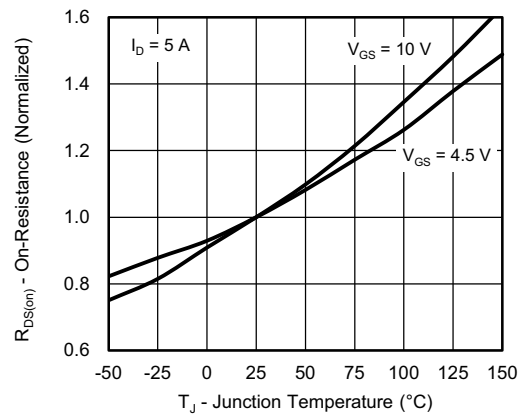
On-Resistance vs. Drain Current



Capacitance

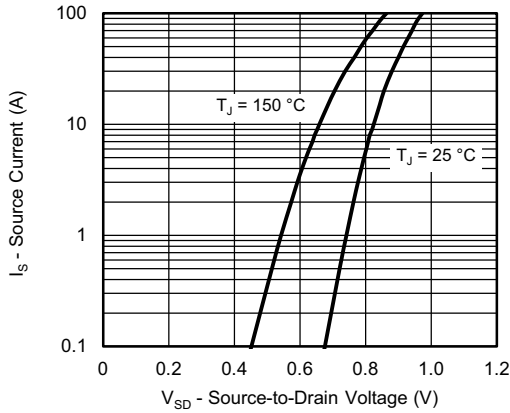


Gate Charge

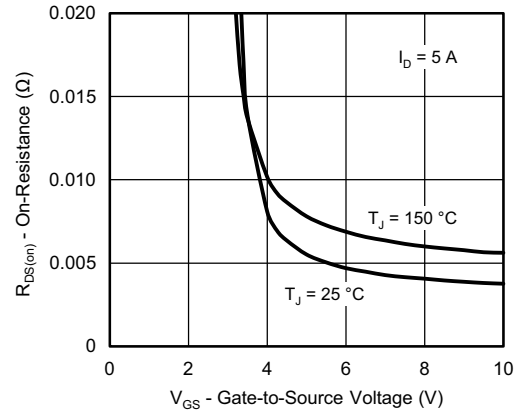


On-Resistance vs. Junction Temperature

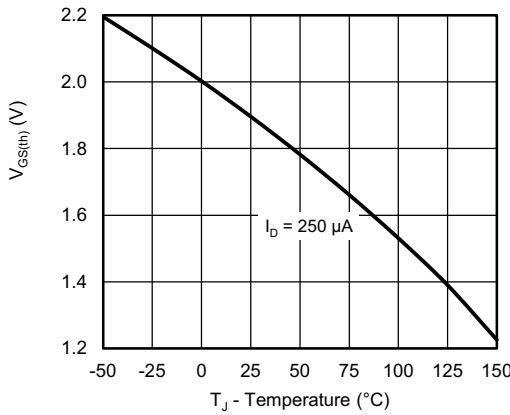
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



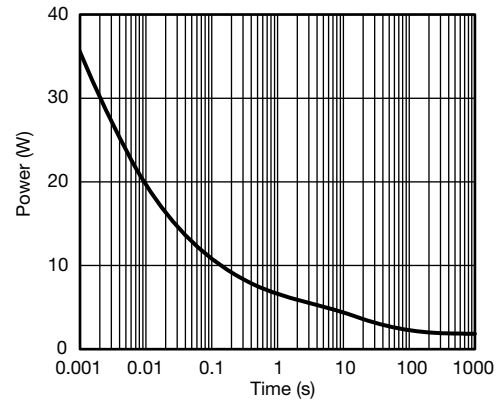
Source-Drain Diode Forward Voltage



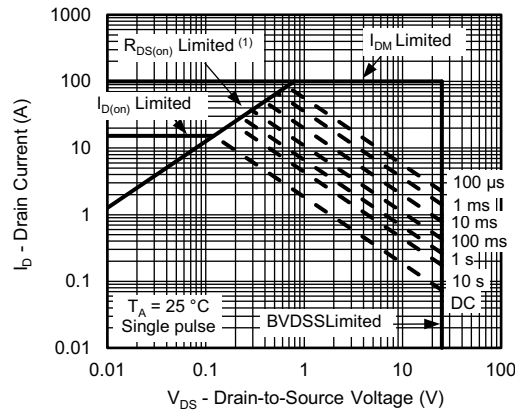
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



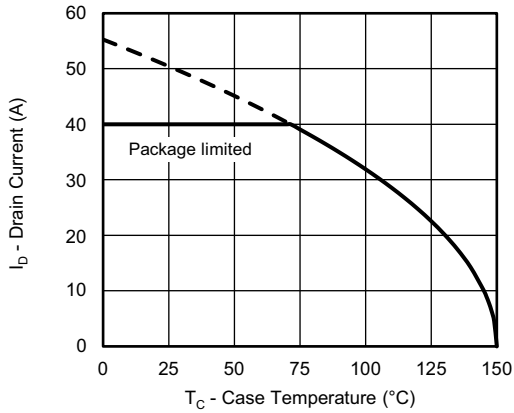
Single Pulse Power, Junction-to-Ambient



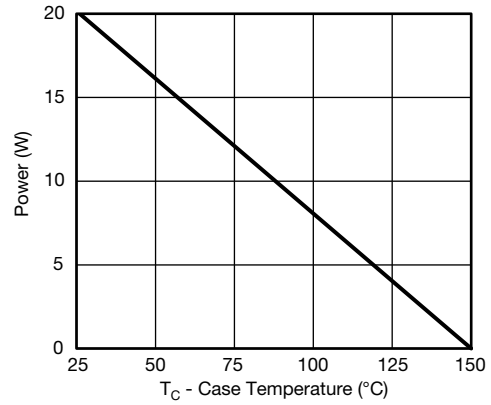
Safe Operating Area, Junction-to-Ambient



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



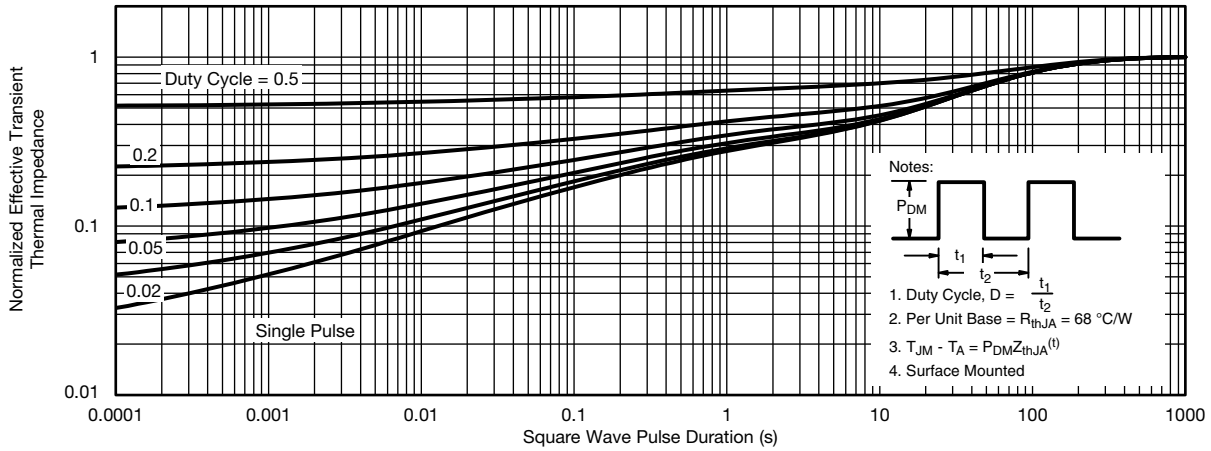
Power, Junction-to-Case

Note

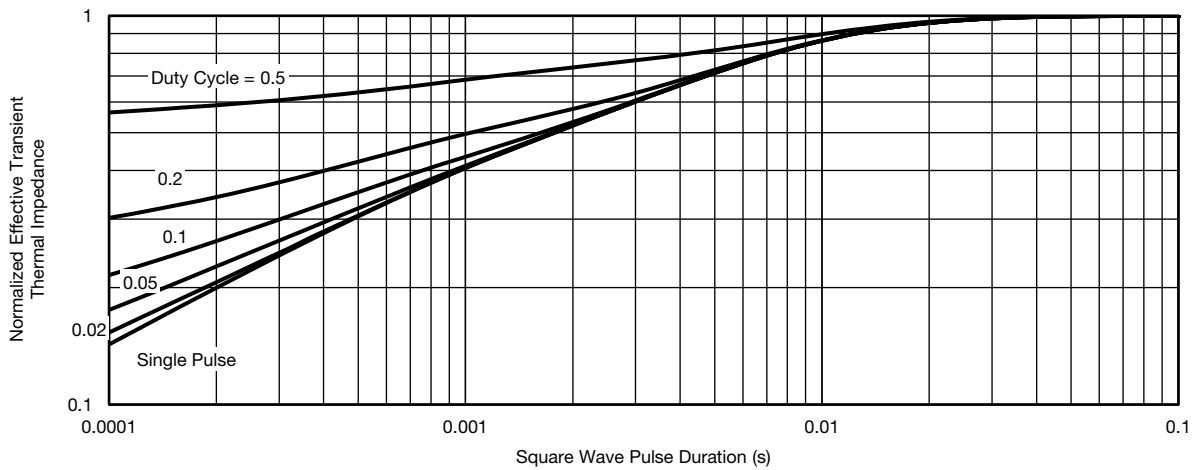
- a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

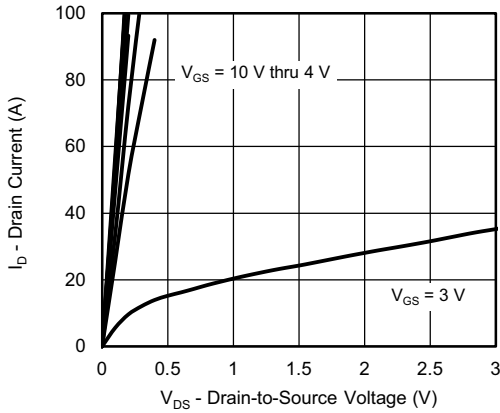


Normalized Thermal Transient Impedance, Junction-to-Ambient

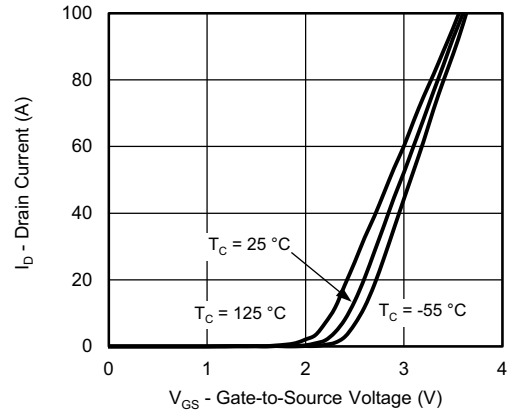


Normalized Thermal Transient Impedance, Junction-to-Case

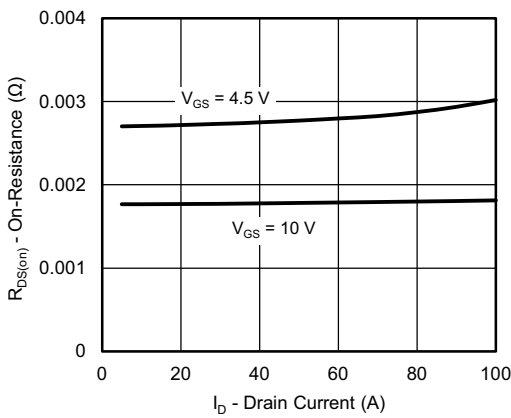
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



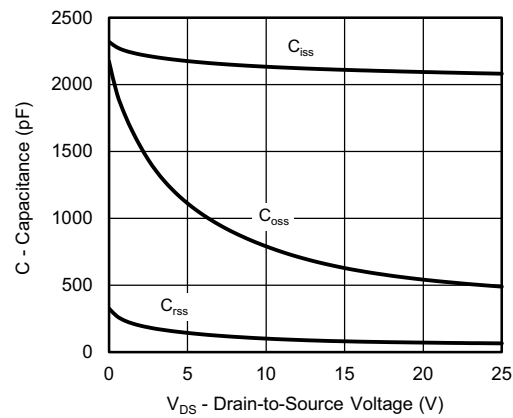
Output Characteristics



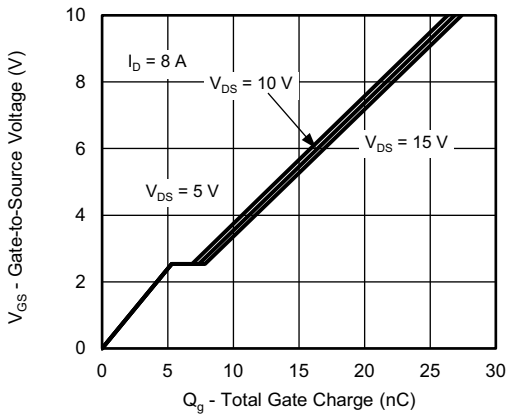
Transfer Characteristics



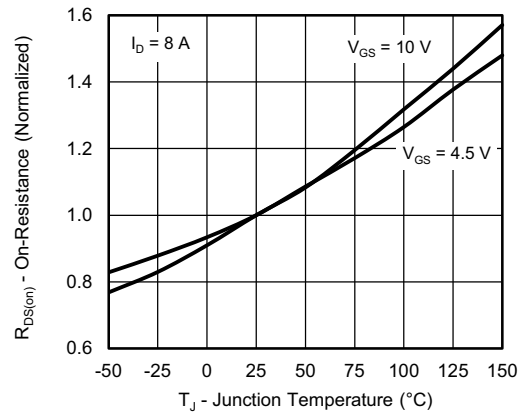
On-Resistance vs. Drain Current



Capacitance



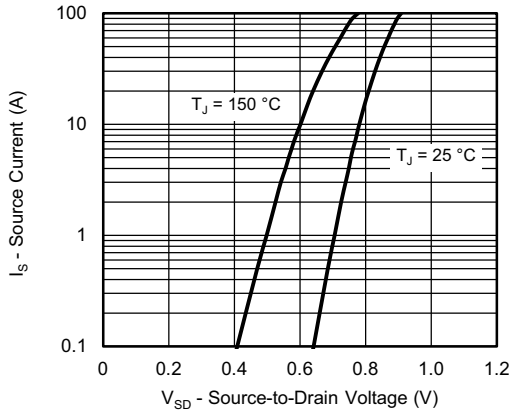
Gate Charge



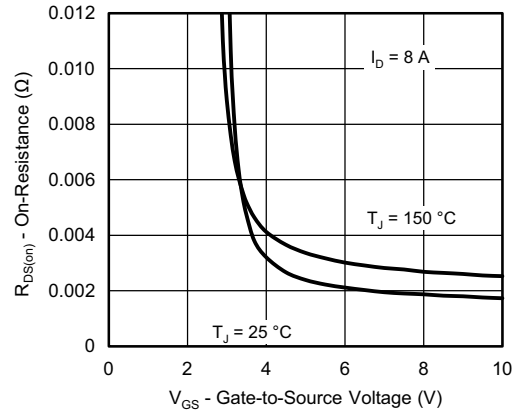
On-Resistance vs. Junction Temperature



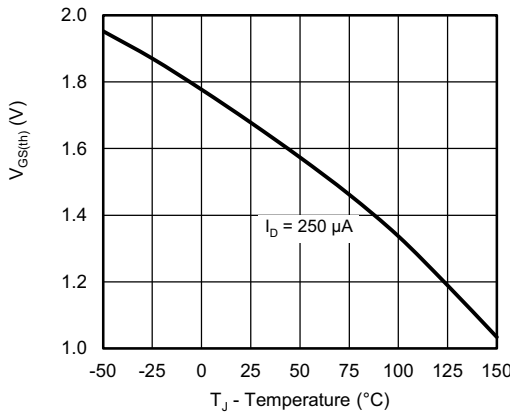
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



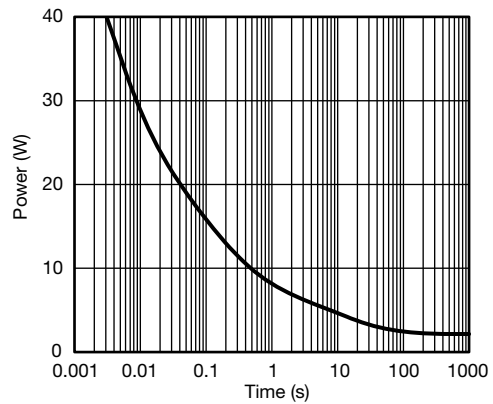
Source-Drain Diode Forward Voltage



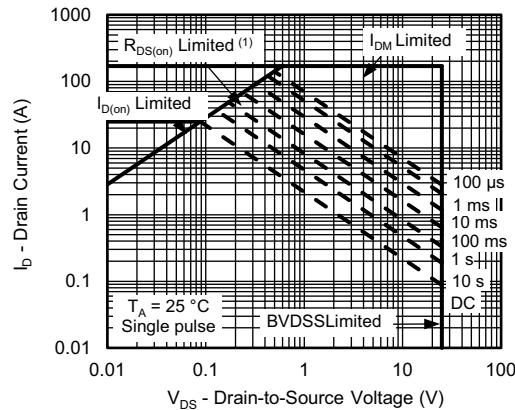
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



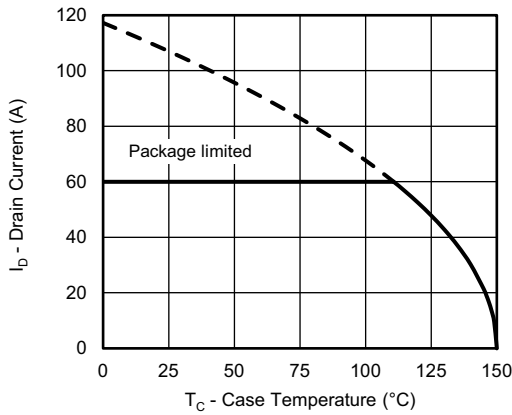
Single Pulse Power, Junction-to-Ambient



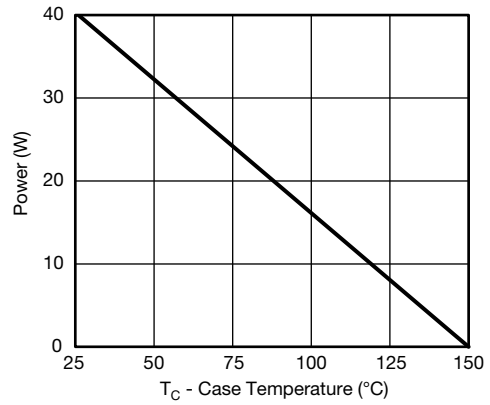
Safe Operating Area, Junction-to-Ambient



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



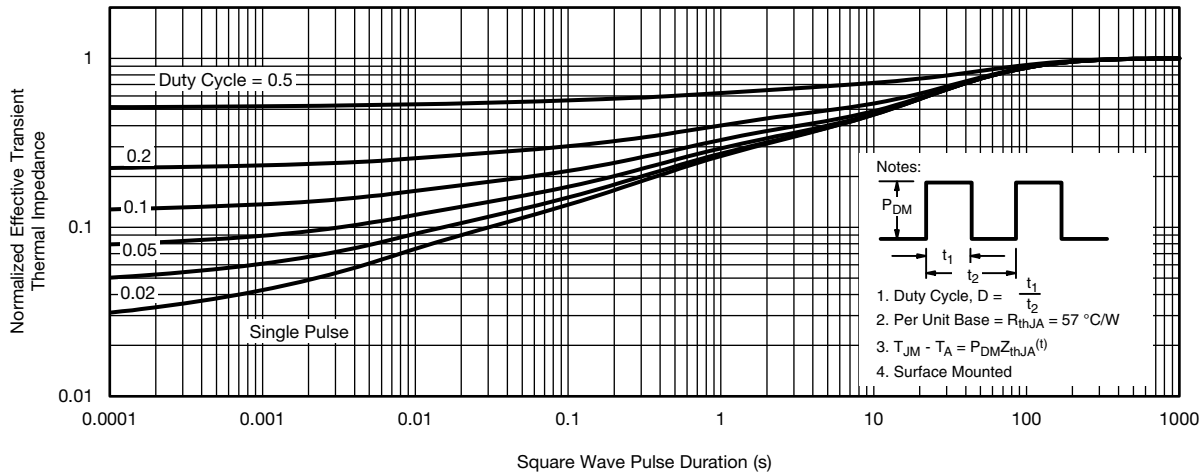
Power, Junction-to-Case

Note

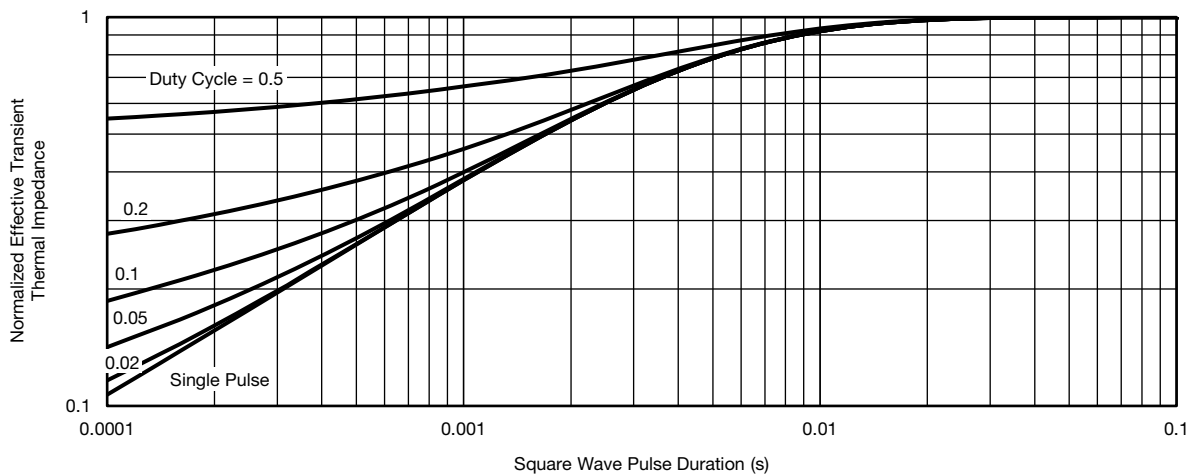
- a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68127.



PowerPAIR® 6 x 5 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	-	0.10	0.000	-	0.004
A3	0.15	0.20	0.25	0.006	0.007	0.009
b	0.43	0.51	0.61	0.017	0.020	0.024
b1	0.25 BSC			0.010 BSC		
D	4.90	5.00	5.10	0.192	0.196	0.200
D1	3.75	3.80	3.85	0.148	0.150	0.152
E	5.90	6.00	6.10	0.232	0.236	0.240
E1 Option AA (for W/B)	2.62	2.67	2.72	0.103	0.105	0.107
E1 Option AB (for BWL)	2.42	2.47	2.52	0.095	0.097	0.099
E2	0.87	0.92	0.97	0.034	0.036	0.038
e	1.27 BSC			0.050 BSC		
K Option AA (for W/B)	0.45 typ.			0.018 typ.		
K Option AB (for BWL)	0.65 typ.			0.025 typ.		
K1	0.66 typ.			0.025 typ.		
L	0.33	0.43	0.53	0.013	0.017	0.020
L3	0.23 BSC			0.009 BSC		
z	0.34 BSC			0.013 BSC		

ECN: T14-0782-Rev. C, 22-Dec-14
 DWG: 6005

Recommended Minimum PAD for PowerPAIR® 6 x 5



Dimensions in millimeters (inch)

Note

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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